

3.3-V, 12-BIT, 30 MSPS, LOW-POWER ANALOG-TO-DIGITAL CONVERTER WITH POWER DOWN

FEATURES

- 12-Bit Resolution, 30 MSPS Analog-to-Digital Converter
- Input Configurations:
 - Differential (0.5x)
 - Differential (1x)
- 3.3-V Supply Operation
- Internal Voltage Reference
- Out-of-Range Indicator
- Power-Down Mode
- IF Undersampling

APPLICATIONS

- Set Top Box (STB)
- Camcorders
- Digital Cameras
- Copiers
- Communications
- Test Instruments
- IF and Baseband Digitization

DW OR PW PACKAGE (TOP VIEW) 28 CLK AGND ∏ 1 CON1 II 2 27 AVDD CON0 [] 3 26 OE 25 D0 EXTREF [] 4 AIN+ **1** 5 24 D1 AIN- ∏ 6 23 D2 22 D3 AGND 7 AV_{DD} [] 8 21 D4 20 DV_{DD} REFT 9 REFB [] 10 19 DGND 18 D5 OVRNG 1 11 17 D6 D11 🛚 12 D10 13 16 D7 15 D9 D8

DESCRIPTION

The THS1230 is a CMOS, low-power, 12-bit, 30 MSPS analog-to-digital converter (ADC) that operates with a 3.3-V supply. The THS1230 gives circuit developers complete flexibility. The analog input to the THS1230 is differential with a gain of 0.5 for Mode 2 and 1.0 for Mode 1. The THS1230 provides a wide selection of voltage references to match the user's design requirements. For more design flexibility, the internal reference can be bypassed to use an external reference to suit the dc accuracy and temperature drift requirements of the application. The out-of-range output is used to monitor any out-of-range condition in the THS1230's input range.

The speed, resolution, and single-supply operation of the THS1230 are suited for applications in set top box (STB), video, multimedia, high-speed acquisition, and communications. The speed and resolution ideally suit charge-couple device (CCD) input systems such as digital copiers, digital cameras, and camcorders. The wide input voltage range between V_{REFB} and V_{REFT} allows the THS1230 to be designed into multiple systems.

The THS1230C is characterized for operation from 0°C to 70°C. The THS1230I is characterized for operation from -40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

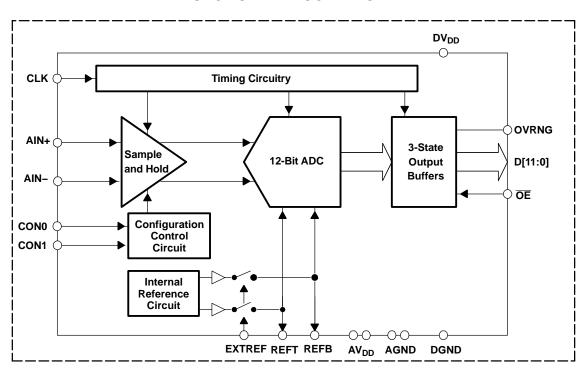
ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION

PRODUCT	PACKAGE- LEAD	PACKAGE DESIGNATOR (1)	SPECIFIED TEMPERATURE RANGE	PACKAGE MARKING	ORDERING NUMBER	TRANSPORT MEDIA, QUANTITY
THS1230	TSSOP-28	PW	0°C to 70°C	TH1230	THS1230CPW	Tube, 50
THS1230	TSSOP-28	PW	0°C to 70°C	TH1230	THS1230CPWR	Tape and reel, 2000
THS1230	TSSOP-28	PW	-40°C to 85°C	TJ1230	THS1230IPW	Tube, 50
THS1230	TSSOP-28	PW	-40°C to 85°C	TJ1230	THS1230IPWR	Tape and reel, 2000
THS1230	SOP-28	DW	0°C to 70°C	TH1230	THS1230CDW	Tube, 20
THS1230	SOP-28	DW	0°C to 70°C	TH1230	THS1230CDWR	Tape and reel, 1000
THS1230	SOP-28	DW	-40°C to 85°C	TJ1230	THS1230IDW	Tube, 20
THS1230	SOP-28	DW	-40°C to 85°C	TJ1230	THS1230IDWR	Tape and reel, 1000

⁽¹⁾ For the most current specifictions and package information refer to our Web site at www.ti.com.

FUNCTIONAL BLOCK DIAGRAM





TERMINAL FUNCTIONS

TERMINAL			DESCRIPTION						
NAME	NO.	I/O	DESCRIPTION						
AGND	1, 7	1	Analog ground						
AV_{DD}	8, 27	I	Analog supply						
AIN+	5	I	Positive analog input						
AIN-	6	I	gative analog input						
CLK	28	I	ADC conversion clock						
CON1	2	I	Configuration input 1						
CON0	3	1	Configuration input 0						
DGND	19	I	Digital ground						
DV _{DD}	20	1	Digital supply						
D11	12	0	ADC data bit 11						
D10	13	0	ADC data bit 10						
D9	14	0	ADC data bit 9						
D8	15	0	ADC data bit 8						
D7	16	0	ADC data bit 7						
D6	17	0	ADC data bit 6						
D5	18	0	ADC data bit 5						
D4	21	0	ADC data bit 4						
D3	22	0	ADC data bit 3						
D2	23	0	ADC data bit 2						
D1	24	0	ADC data bit 1						
D0	25	0	ADC data bit 0						
EXTRE	F 4	1	Reference select input (high = external, low = internal)						
OVRNO	3 11	0	Out of range indicator (high = out of range)						
ŌĒ	26	I	Output enable (high = disable, low = enable)						
REFT	9	I/O	Upper ADC reference voltage						
REFB	10	I/O	Lower ADC reference voltage						

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		UNIT	
Complementary	AV _{DD} to AGND, DV _{DD} to DGND	-0.3 V to 4 V	
Supply voltage range	AGND to DGND	-0.3 V to 4 V -0.3 V to 0.3 V -0.3 to AV _{DD} + 0.3 V -0.3 to AV _{DD} + 0.3 V -0.3 to AV _{DD} + 0.3 V -0.3 to DV _{DD} + 0.3 V -0.3 to DV _{DD} + 0.3 V -0.3 to DV _{DD} + 0.3 V	
Reference voltage input r	ange, REFT, REFB to AGND	-0.3 to AV _{DD} + 0.3 V	
Analog input voltage rang	e, AIN+, AIN- to AGND	-0.3 to AV _{DD} + 0.3 V	
Clock input voltage range, CLK to AGND -0.3 to AV			
Digital input voltage range	e, digital input to DGND	-0.3 to DV _{DD} + 0.3 V	
Digital output voltage ran	ge, digital output to DGND	-0.3 to DV _{DD} + 0.3 V	
Operating junction tempe	rature range, T _J	-40°C to 150°C	
Storage temperature rang	ge, T _{STG}	− 65°C to 150°C	
Lead temperature 1,6 mn	n (1/16 in) from case for 10 seconds	300°C	

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range, $T_{\rm A}$ (unless otherwise noted)

			MIN	NOM	MAX	UNIT
POWER SUPPLY						
Supply voltage	AV _{DD} DV _{DD}		3.0	3.3	3.6	V
ANALOG AND REFERENCE INP	PUTS		•			
Reference input voltage	V _{REFT}	f _{CLK} = 5 MHz to 30 MHz	2.0	2.15	2.5	V
	V_{REFB}	f _{CLK} = 5 MHz to 30 MHz	1.05	1.15	1.3	
Reference voltage differential, V _{RE}	FT - V _{REFB}	f _{CLK} = 5 MHz to 30 MHz	0.95	1.0	1.05	V
Analog input voltage differential, (A	AIN+) – (AIN–) ⁽¹⁾	CON1 = 0, CON0 = 1	-1.0		1.0	V
		CON1 = 1, CON0 = 0	-2.0		2.0	
Analog input capacitance, C _i			10	pF		
Clock input (2)	0		AV_{DD}	V		
DIGITAL OUTPUTS			•			
Minimum digital output load resista	ance, R _L		100			kΩ
Maximum digital output load capa	citance, C _i		0	10	15	pF
DIGITAL INPUTS						
High-level input voltage, V _{IH}			2.4		DV_DD	V
Low-level input voltage, V _{IL}	DGND		0.8	V		
Clock frequency, f _{CLK} ⁽³⁾					30	MHz
Clock pulse duration, tw(CLKL), tw(C	LKH)	f _{CLK} = 30 MHz	15	16.7	18.3	ns
Operating free-air temperature, T		TH1230	0		70	°C
		TJ1230	-40		85	

 ⁽¹⁾ Based on V_{REFT} - V_{REFB} = 1.0 V, varies proportional to the V_{REFT} - V_{REFB} value. AIN+ and AIN- inputs must always be greater than 0 V and less than AV_{DD}.
 (2) Clock pin is referenced to AGND and powered by AV_{DD}.
 (3) Clock frequency can be extended to this range without degradation of performance.



ELECTRICAL CHARACTERISTICS

over recommended operating conditions (AV_{DD} = DV_{DD} = 3.3 V, f_s = 30 MHz/50% duty cycle, MODE = 1, 1-V input span, internal reference, T_{min} to T_{max}) (unless otherwise noted)

DIGITAL I	NPUTS AND OUTPUTS (ALL	SUPPLIES = 3.3 V)						
	PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT	
DIGITAL I	NPUTS		•		-			
.,	LPak Level Count on Rene	All other inputs		$0.8 \times DV_{DD}$.,	
V _{IH}	High level input voltage	CLK		$0.8 \times AV_{DD}$			V	
\/	Lavelaval innerteentari	All other inputs				$0.2 \times \mathrm{DV}_\mathrm{DD}$	V	
V _{IL}	Low level input voltage	CLK				$0.2 \times \text{AV}_{\text{DD}}$	V	
I _{IH}	High level input current	•				1	μΑ	
I _{IL}	Low level input current					-1	μA	
C _i	Input capacitance				5		pF	
DIGITAL O	DUTPUTS		•					
V _{OH}	High level output voltage		$I_{load} = 50 \mu A$	DV _{DD} -0.4			V	
V _{OL}	Low level output voltage		$I_{load} = -50 \mu A$			0.4	V	
	High impedance output cur	rent				±1	μΑ	
t _r /t _f	Rise/fall time		C _L = 10 pF		4.5		ns	
ANALOG	INPUTS		•					
C _i	Switched input capacitance				6		pF	
t _{d(ap)}	Aperture delay time				2		ns	
	Aperture uncertainty (jitter)				2		ps	
	DC leakage current (input	= ±FS)			10		μA	
POWER S	SUPPLY (CLK = 30 MHz)		•					
XV_{DD}	Supply voltage (all supplies	s)		3	3.3	3.6	V	
I _{DD}	Supply current active - tota	I			48	66		
I _(analog)	Supply current active - ana	log			35		mA	
I _(digital)	Supply current active - digi	tal			13			
I _{I(standby)}	Standby supply current		CLK = 0 MHz			10	μA	
	Dower up time for reference	as from atomalou	1 μF Bypass ⁽¹⁾		770		μs	
t _(PU)	Power-up time for reference	es from standby	10 μF Bypass ⁽¹⁾		6.2		ms	
t _(PUconv)	Power-up time for valid AD	C conversions	See Note (2)		720		ns	
В	Dower dissinction		See Note (3)		168	220	m\//	
P _D	Power dissipation		See Note (4)		188		mW	
P _{D(STBY)}	Standby power dissipation	·	CLK = 0 MHz			36	μW	
PSRR	Power supply rejection ration	0			±0.1		%FS	

⁽¹⁾ Time for reference to recover to 1% of its final voltage level.

⁽²⁾ Time for ADC conversions to be accurate to within 0.1% of fullscale, INT ckts.

⁽³⁾ Clock = 30 MHz, AIN+ and AIN- at Common Mode or 1.65 V DC.

⁽⁴⁾ Clock = 30 MHz, fin = 3.58 MHz at -1 dBFS.



ELECTRICAL CHARACTERISTICS (CONTINUED)

over recommended operating conditions (AV_{DD} = DV_{DD} = 3.3 V, f_s = 30 MHz/50% duty cycle, MODE = 1, 1-V input span, internal reference, T_{min} to T_{max}) (unless otherwise noted)

REFT, REFB REFERENCE VOLTAGES (all supplies = 3.3 V)									
	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT			
INTERN	NAL REFERENCE ⁽¹⁾	•							
V _{REFT}	Upper reference voltage			2.15					
V _{REFB}	Lower reference voltage			1.15		V			
V _{REF}	Differential reference voltage, V _{REFT} – V _{REFB}		0.95	1	1.05				
	Differential reference voltage, V _{REFT} – V _{REFB} accuracy		-5%		5%				
EXTER	NAL REFERENCE								
	Externally applied V _{REFT} reference voltage range		2		2.5				
	Externally applied V _{REFB} reference voltage range		1.05		1.3	V			
	Externally applied (V _{REFT} – V _{REFB}) reference voltage range		0.75		1.05				
	External mode V _{REFT} to V _{REFB} impedance			9		kΩ			
INTERN	NAL OR EXTERNAL REFERENCE								
C _T	V _{REFT} decoupling capacitor value			0.1					
СВ	V _{REFB} decoupling capacitor value			0.1		μF			
C _{TB}	Decoupling capacitor V _{REFT} to V _{REFB}			10					

(1) The internal reference voltage is not intended for use driving off chip.

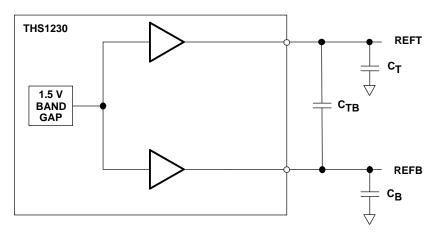


Figure 1. Reference Generation



ELECTRICAL CHARACTERISTICS (CONTINUED)

over recommended operating conditions (AV_{DD} = DV_{DD} = 3.3 V, f_s = 30 MHz/50% duty cycle, MODE = 1, 1-V input span, internal reference, T_{min} to T_{max}) (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
DC ACC	CURACY (LINEARITY)	•							
	Number of missing codes	All modes			0	codes			
DNL	Differential nonlinearity	All modes		±0.4	±1	LSB			
INL	Integral nonlinearity	All modes	-2.5	±1.2	2	LSB			
	Offset error	All modes		0.7	1.2	%FSR			
	Gain error	All modes		1.1	3.5	%FSR			
DYNAM	IIC PERFORMANCE ⁽¹⁾	•							
		f _i = 3.58 MHz		10.9					
ENOB	Effective number of bits	$f_i = 10 \text{ MHz}$	10.4	10.6		Bits			
		f _i = 15 MHz		10.4					
		f _i = 3.58 MHz		-76					
THD	Total harmonic distortion	f _i = 10 MHz		-74	-65	dB			
		$f_i = 15 \text{ MHz}$		-72.5					
		f _i = 3.58 MHz		68					
SNR	Signal-to-noise ratio	f _i = 10 MHz	64.5	65.6		dB			
		$f_i = 15 \text{ MHz}$		64.6					
		f _i = 3.58 MHz		67.4					
SINAD	Signal-to-noise + distortion	f _i = 10 MHz	64	65		dB			
		f _i = 15 MHz		64.5					
		f _i = 3.58 MHz		78.1					
SFDR	Spurious free dynamic range	f _i = 10 MHz	67	74		dB			
		f _i = 15 MHz		72					
	Analog input bandwidth			180		MHz			
	Differential phase, DP			0.12		degree			
G _(diff)	Differential gain			0.01%					
TIMING	(all supplies = 3.3 V)								
f _{CLK}	Clock frequency ⁽²⁾		5		30	MHz			
OLIX	Clock duty cycle		45%	50%	55%				
t _{d(O)}	Output delay time			7	19	ns			
$t_{d(PZ)}$	Delay time, output disable to Hi-Z output			3.2		ns			
$t_{d(EN)}$	Delay time, output enable to output valid			5	19	ns			
	Latency				5	cycles			

Input amplitudes for all single tone dynamic tests are at -1 dBFS, all supplies = 3.3 V. The clock frequency may be extended to 5 MHz without degradation in specified performance.



Hi-Z

PARAMETER MEASUREMENT INFORMATION

TIMING DIAGRAM

Hi-Z

D[9:0] •

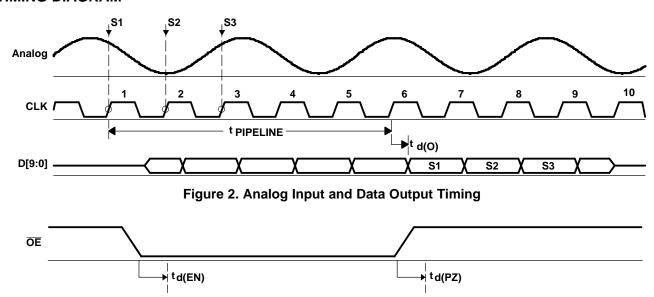


Figure 3. Output Enable Timing

Data

Data

Data



TYPICAL CHARACTERISTICS

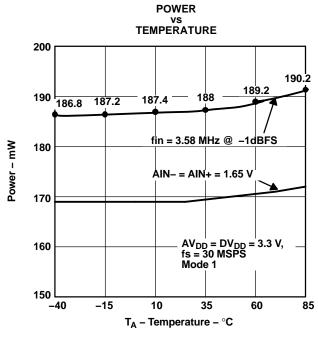


Figure 4.

SPURIOUS FREE DYNAMIC RANGE

vs TEMPERATURE

75

-40

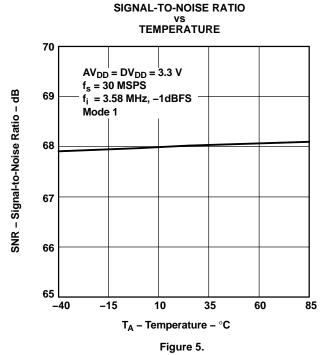
-15

 T_A – Temperature – °C Figure 6.

35

60

85





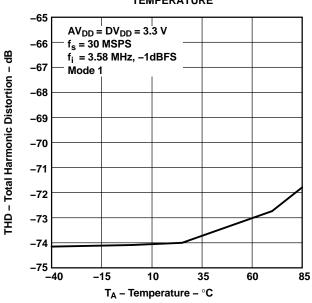


Figure 7.



TYPICAL CHARACTERISTICS (continued)

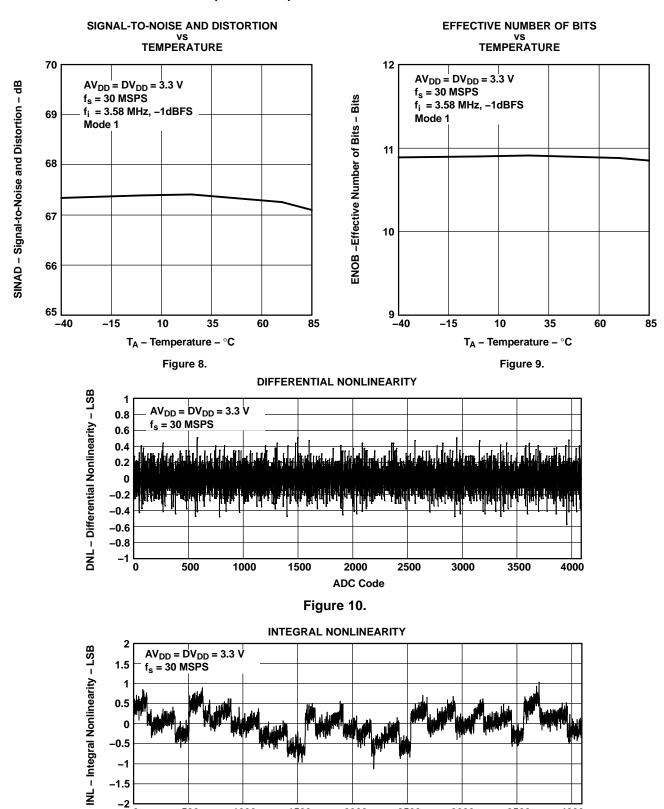


Figure 11.

ADC Code



TYPICAL CHARACTERISTICS (continued)

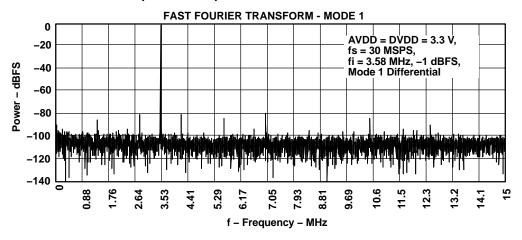
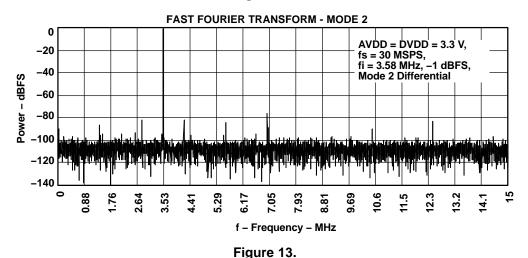


Figure 12.



PRINCIPLES OF OPERATION

Analog Input

The analog input AIN is sampled in the sample and hold unit, the output of which feeds the ADC CORE, where the process of analog to digital conversion is performed against ADC reference voltages, V_{REFT} and V_{REFB} .

Connecting the EXTREF pin to one of two voltages, DGND or DV_{DD} selects one of the two configurations of ADC reference generation. The ADC reference voltages come from either the internal reference buffer or completely external sources. Connect EXTREF to DGND for internal reference generation or to DV_{DD} for external reference generation.

CON0 and CON1 as described below, select the input configuration mode or place the device in powerdown. The ADC core drives out through output buffers to the data pins D0 to D11. The output buffers can be disabled by the \overline{OE} pin.

A single, sample-rate clock (30 MHz maximum) is required at pin CLK. The analog input signal is sampled on the rising edge of CLK, and corresponding data is output after the fifth following rising edge.

The THS1230 can operate in differential Mode 1 or differential Mode 2, controlled by the configuration pins CON0 and CON1 as shown in Table 1. Mode 0 places the device in power-down state or standby for reduced power consumption.



Table 1. Input Modes of Operation

MODE	CON1	CON0	MODE OF OPERATION
0	0	0	Device powered down
1	0	1	Differential mode × 1
2	1	0	Differential mode × 0.5
3	1	1	Not used

Modes 1 and 2 are shown in Figure 14.

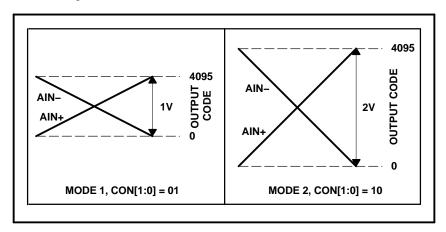


Figure 14. Input Mode Configurations

The gain of the sample and hold changes with the CON1 and the CON0 inputs. Table 2 shows the gain of the sample and hold and the levels applied at the AIN+ and AIN- analog inputs for Mode 1 and Mode 2. The common mode level for the two analog inputs is at AVDD/2.

Table 2. Input Mode Switching

MODE	CON1	CON0	(AIN+) - (AIN-) MIN	(AIN+) – (AIN–) MAX	S/H GAIN	
1	0	1	-1 V	1 V	×1	
2	1	0	–2 V	2 V	×0.5	

Table 2 assumes that the delta in ADC reference voltages V_{REFT} and V_{REFB} is set to 1 V, i.e., $V_{REFT} - V_{REFB} = 1$ V. Note that V_{REFB} and V_{REFT} can be set externally, which will scale the numbers given in this table.

The user-chosen operating configuration and reference voltages determine what input signal voltage range the THS1230 can handle.

The following sections explain both the internal signal flow of the device and how the input signal span is related to the ADC reference voltages, as well as the ways in which the ADC reference voltages can be buffered internally or externally applied.

Signal Processing Chain (Sample and Hold, ADC)

Figure 15 shows the signal flow through the sample and hold unit and the PGA to the ADC core.



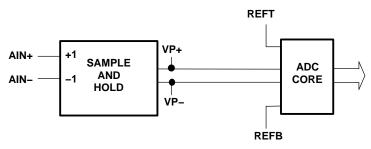


Figure 15. Analog Input Signal Flow

Sample and Hold

The differential sample and hold processes A_{IN} with respect to the voltages applied to the REFT and REFB pins, to give a differential output (VP+) – (VP–) = VP given by:

• VP = (AIN+) - (AIN-)

Analog-to-Digital Converter

No matter what operating configuration is chosen, VP is digitized against ADC reference voltages V_{REFT} and V_{REFB} . The V_{REFT} and V_{REFB} voltages set the analog input span limits FS+ and FS-, respectively. Any voltages at AIN greater than REFT or less than REFB causes ADC over-range, which is signaled by OVR going high when the conversion result is output.

Analog Input

A first-order approximation for the equivalent analog input circuit of the THS1230 is shown in Figure 16. The equivalent input capacitance C_l is 5 pF typical. The input must charge/discharge this capacitance within the sample period of one half of a clock cycle. When a full-scale voltage step is applied, the input source provides the charging current through the switch resistance R_{SW} (200 Ω) of S1 and quickly settles. In this case the input impedance is low. Alternatively, when the source voltage equals the value previously stored on C_l , the hold capacitor requires no input current and the equivalent input impedance is very high.

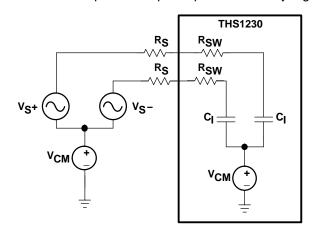


Figure 16. Simplified Equivalent Input Circuit

To maintain the frequency performance outlined in the specifications, the total source impedance should be limited to the following equation with $f_{CLK} = 30$ MHz, $C_I = 5$ pF, $R_{SW} = 200$ Ω :

$$\mathsf{R}_{S} < \frac{1}{2^f_{CLK} \times C_I \times In(256)} \text{--} \mathsf{R}_{SW}$$

So, for applications running at a lower f_{CLK} , the total source resistance can increase proportionally.



The analog input of the THS1230 is a differential input that can be configured in various ways depending on the signal source and the required level of performance. A fully differential connection (see Figure 17) delivers the best performance from the converter.

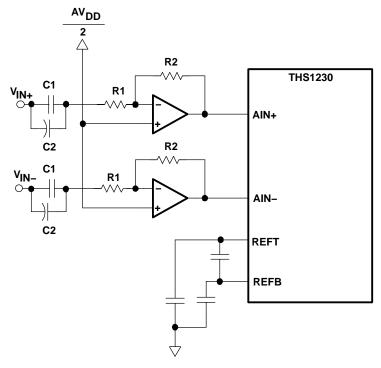


Figure 17. AC-Coupled Differential Input

The analog input can be dc-coupled (see Figure 18) as long as the inputs are within the analog input common mode voltage range. For example (see Figure 18), V+ and V- are signals centered on GND with a peak-to-peak voltage of 2 V, and the circuit in Figure 18 is used to interface it with the THS1230. Assume AV_{DD} of the converter is 3 V. Two problems have to be solved. The first is to shift common mode level (CML) from 0 V to 1.5 V (AV_{DD}/2). To do that, a V bias voltage and an adequate ratio of R1 and R2 have to be selected. For instance, if V bias = AV_{DD} = 3 V, then R1 = R2. The second is that the differential voltage has to be reduced from 4 V (2 x 2 V) to 1 V, and for that an attenuation of 4 to1 is needed. The attenuation is determined by the relation: (R3||2R2)/((R3||2R2) + 2R1). One possible solution is R1 = R2 = R3 = 150 Ω . In this case, moreover, the input impedance (2R1 + (R3||2R2)) will be 400 Ω . The values can be changed to match any other input impedance. A capacitor, C, connected from AIN+ to AIN- helps filter any high frequency noise on the inputs, also improving performance. Note that the chosen value of capacitor C must take into account the highest frequency component of the analog input signal.



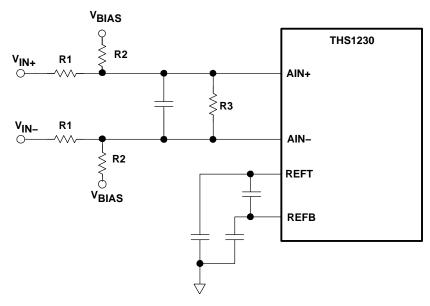


Figure 18. DC-Coupled Differential Input Circuit

A single-ended source may give better overall system performance when it is converted to a differential signal before driving the THS1230. The configuration in Figure 19 takes a VIN of 1 V and drives the 1:1 transformer ratio so that value of AIN+ and AIN- converts to fullscale value at the ADC digital output. With VIN at -1 V the value at AIN+ and AIN- converts to 0 at the ADC digital outputs.

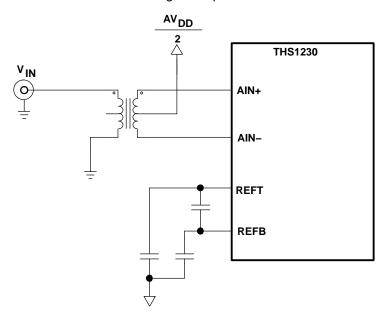


Figure 19. Transformer Coupled Single-Ended Input

Digital Outputs

The output of THS1230 is in unsigned binary code. The ADC input over-range indicator is output on pin OVRNG. Capacitive loading on the output should be kept as low as possible (a maximum loading of 10 pF is recommended) to ensure best performance. Higher output loading causes higher dynamic output currents and can therefore increase noise coupling into the part's analog front end. To drive higher loads the use of an output buffer is recommended.



When clocking output data from THS1230, it is important to observe its timing relation to CLK. The pipeline ADC delay is 5 clock cycles to which the maximum output propagation delay needs to be added.

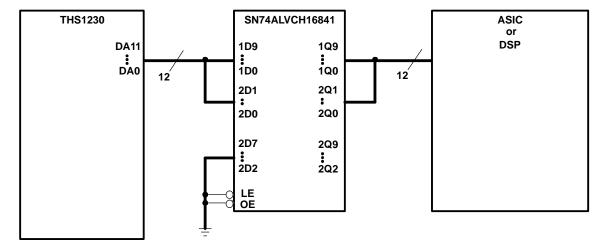


Figure 20. Buffered Output Connection

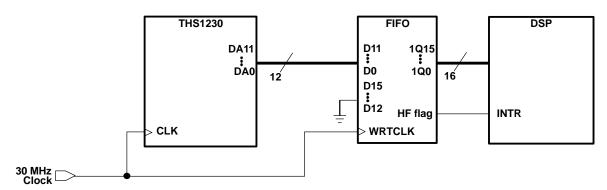


Figure 21. FIFO Connection

Layout, Decoupling and Grounding Rules

Proper grounding and layout of the PCB on which THS1230 is populated is essential to achieve the stated performance. It is advised to use separate analog and digital ground planes that are spliced underneath the IC. THS1230 has digital and analog pins on opposite sides of the package to make this easier. Because there is no connection internally between analog and digital grounds, they have to be joined on the PCB. It is advised to do this at one point in close proximity to THS1230.

Because of the high sampling rate and switched-capacitor architecture, THS1230 generates transients on the supply and reference lines. Proper decoupling of these lines is therefore essential. Decoupling is recommended as shown in the schematic of the THS1230 evaluation module in Figure 22.



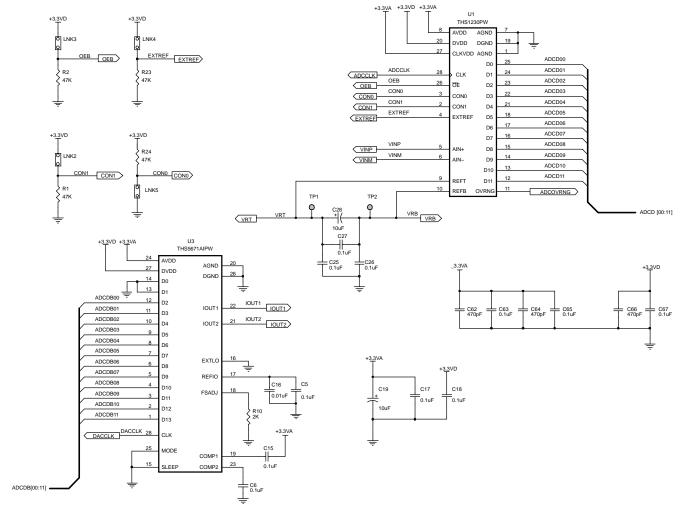


Figure 22. EVM Schematic

DEFINITIONS OF SPECIFICATIONS AND TERMINOLOGY

Integral Nonlinearity (INL)

Integral nonlinearity refers to the deviation of each individual code from a line drawn from zero through full scale. The point used as zero occurs 1/2 LSB before the first code transition. The full-scale point is defined as level 1/2 LSB beyond the last code transition. The deviation is measured from the center of each particular code to the true straight line between these two end-points.

Differential Nonlinearity (DNL)

An ideal ADC exhibits code transitions that are exactly 1 LSB apart. DNL is the deviation from this ideal value. Therefore, this measure indicates how uniform the transfer function step sizes are. The ideal step size is defined here as the step size for the device under test, i.e. (last transition level - first transition level)/(2n - 2). Using this definition for DNL separates the effects of gain and offset error. A minimum DNL better than -1 LSB ensures no missing codes.

Offset and Gain Error

Offset error (in LSBs) is defined as the average offset for all inputs, and gain error is defined as the maximum error (in LSBs) caused by the angular deviation from the offset corrected straight line.



Analog Input Bandwidth

The analog input bandwidth is defined as the maximum frequency of a 1-dBFS input sine wave that can be applied to the device for which an extra 3-dB attenuation is observed in the reconstructed output signal.

Output Timing

Output timing $t_{d(O)}$ is measured from the 50% level of the CLK input falling edge to the 10%/90% level of the digital output. The digital output load is not higher than 10 pF.

Output hold time $t_{h(O)}$ is measured from the 50% level of the CLK input falling edge to the 10%/90% level of the digital output. The digital output load is not less than 2 pF.

Aperture delay t_{d(A)} is measured from the 50% level of the CLK input to the actual sampling instant.

The OE signal is asynchronous.

OE timing $t_{d(PZ)}$ is measured from the $V_{IH(min)}$ level of OE to the high-impedance state of the output data. The digital output load is not higher than 10 pF.

OE timing $t_{d(EN)}$ is measured from the $V_{IL(max)}$ level of OE to the instant when the output data reaches $V_{OH(min)}$ or $V_{OL(max)}$ output levels. The digital output load is not higher than 10 pF.

Signal-to-Noise Ratio + Distortion (SINAD)

SINAD is the ratio of the rms value of the measured input signal to the rms sum of all other spectral components below the Nyquist frequency, including harmonics but excluding dc. The value for SINAD is expressed in decibels.

Effective Number of Bits (ENOB)

For a sine wave, SINAD can be expressed in terms of the number of bits. Using the following formula,

• N = (SINAD - 1.76)/6.02

it is possible to get a measure of performance expressed as N, the effective number of bits. Thus, effective number of bits for a device for sine wave inputs at a given input frequency can be calculated directly from its measured SINAD.

Total Harmonic Distortion (THD)

THD is the ratio of the rms sum of the first six harmonic components to the rms value of the measured input signal and is expressed as a percentage or in decibels.

Spurious Free Dynamic Range (SFDR)

SFDR is the difference in dB between the rms amplitude of the input signal and the peak spurious signal.



PACKAGE OPTION ADDENDUM

5-Oct-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
THS1230IDW	OBSOLETE	SOIC	DW	28		TBD	Call TI	Call TI	-40 to 85	TJ1230	
THS1230IPW	OBSOLETE	TSSOP	PW	28		TBD	Call TI	Call TI	-40 to 85	TJ1230	
THS1230IPWG4	OBSOLETE	TSSOP	PW	28		TBD	Call TI	Call TI	-40 to 85		

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

5-Oct-2015

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DW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AE.



PW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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